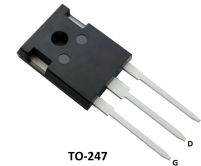
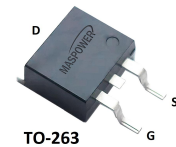
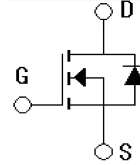


Features

- Very low $R_{DS(on)}$
- Very low Q_g
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant



Applications

- Uninterruptible Power Supply
- Power Factor Correction

Absolute Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	900	V
Transient Gate-Source Voltage	V_{GSM}	± 30	V
Continuous Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current-continuous	$I_D, T=25^\circ\text{C}$ $T=100^\circ\text{C}$	30	A
		22	A
Drain Current-pulse (note 1)	I_{DM}	120	A
Single Pulsed Avalanche Energy (note 2)	E_{AS}	280	mJ
Repetitive Avalanche Energy(note 2)	E_{AR}	0.5	mJ
Avalanche Current	I_{AR}	7.5	A
Power Dissipation	$P_D, T_C=25^\circ\text{C}$ Derate above 25°C	240	W
		1.92	W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

Electrical Characteristics($T_{CASE}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Off-Characteristics						
Drain-Source Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	900	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=900\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=900\text{V}, T_C=150^\circ\text{C}$	-	-	100	μA
Gate body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
On-Characteristics						

Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.7	3.8	5.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =15V, I _D =20A	-	167	222	mΩ
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1.0MHZ	-	2840	-	pF
Output capacitance	C _{oss}		-	220	-	pF
Reverse transfer capacitance	C _{rss}		-	16	-	pF
Switching-Characteristics						
Turn-On delay time	t _{d(on)}	V _{DD} =400V, I _D =30A, R _G =25Ω	-	49	-	ns
Turn-On rise time	t _r		-	42	-	ns
Turn-Off delay time	t _{d(Off)}		-	166	-	ns
Turn-Off rise time	t _f		-	23	-	ns
Total Gate Charge	Q _g	V _{DS} =720V, I _D =30A, V _{GS} =10V	-	62	-	nC
Gate-Source charge	Q _{gs}		-	15	-	nC
Gate-Drain charge	Q _{gd}		-	23	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
Body Diode Forward Current	I _{SD}	T _C =25℃	-	-	30	A
Body Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.68	1.2	V
Reverse recovery time	t _{rr}	V _R =400, I _F =30A dI _F /dt=100A/μs	-	680	-	ns
Reverse recovery charge	Q _{rr}		-	9	-	μC
Peak Reverse Recovery Current	I _{rrm}		-	24	-	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, junction to Case, Max.	$R_{th(j-C)}$	0.52	$^\circ C/W$
Thermal Resistance, junction to Ambient, Max.	$R_{th(j-A)}$	62	$^\circ C/W$

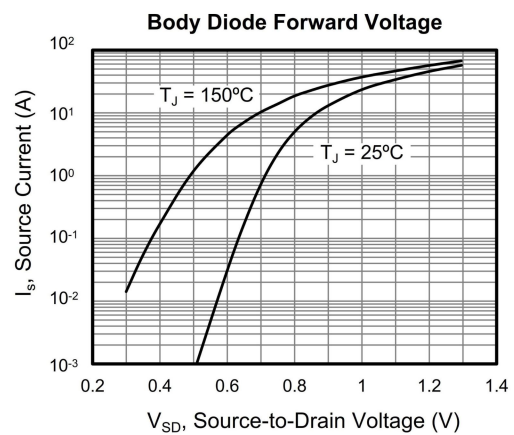
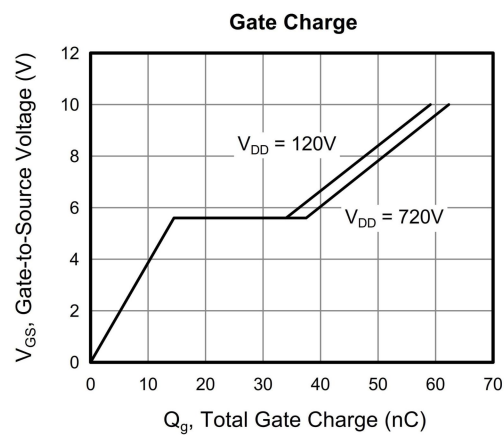
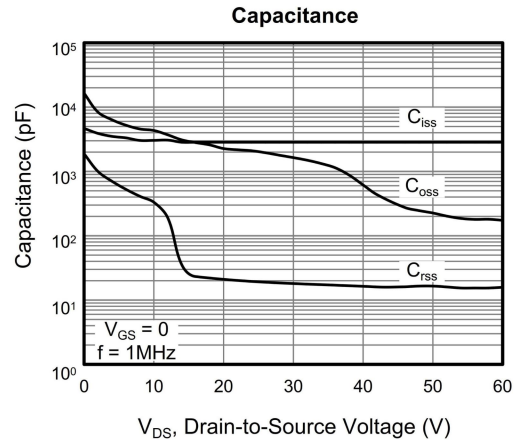
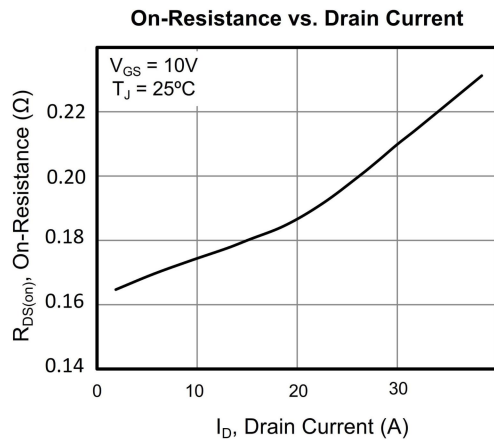
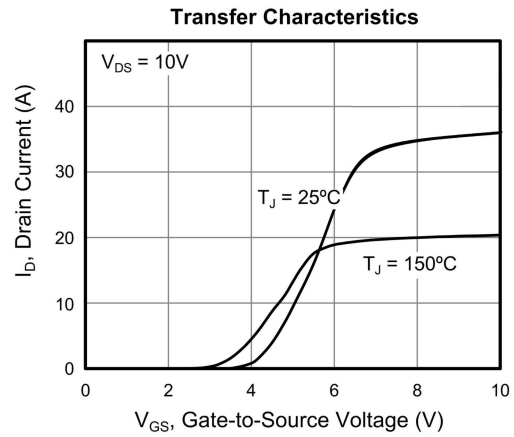
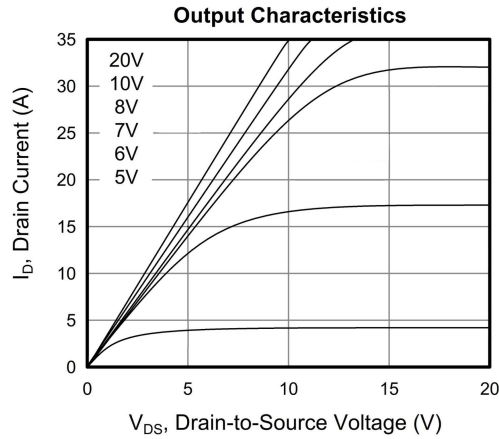
Notes:

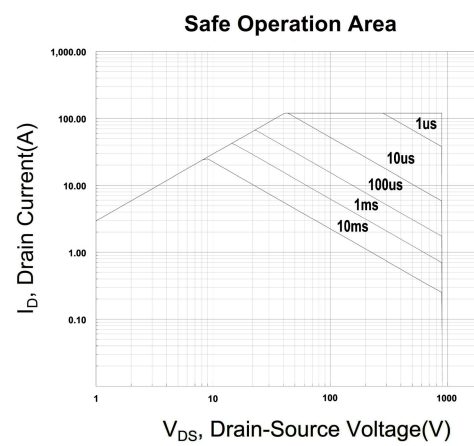
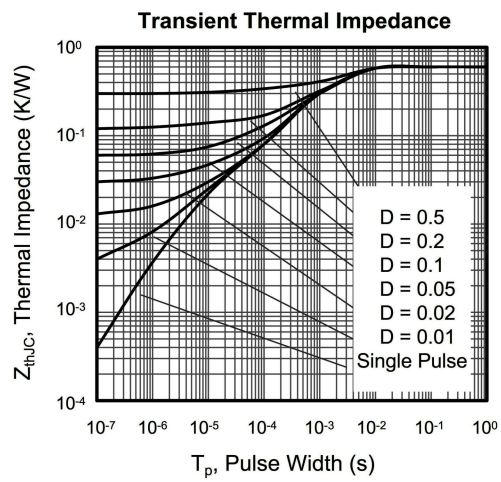
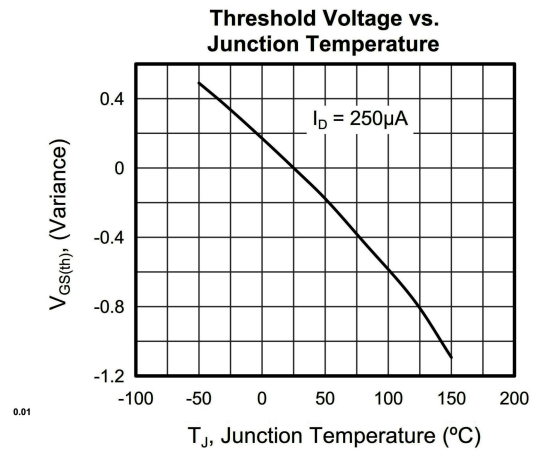
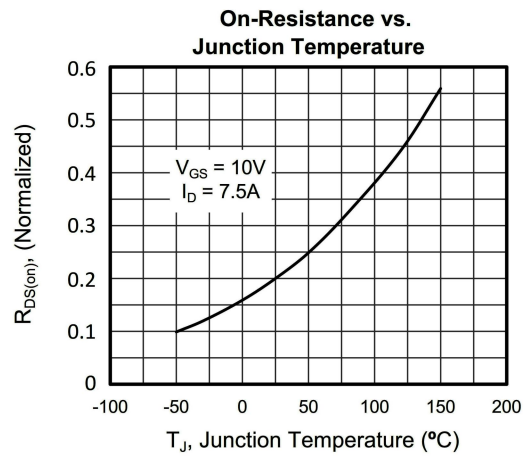
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_D = 10A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ C$
3. Identical low side and high side switch with identical R_G

Order Message

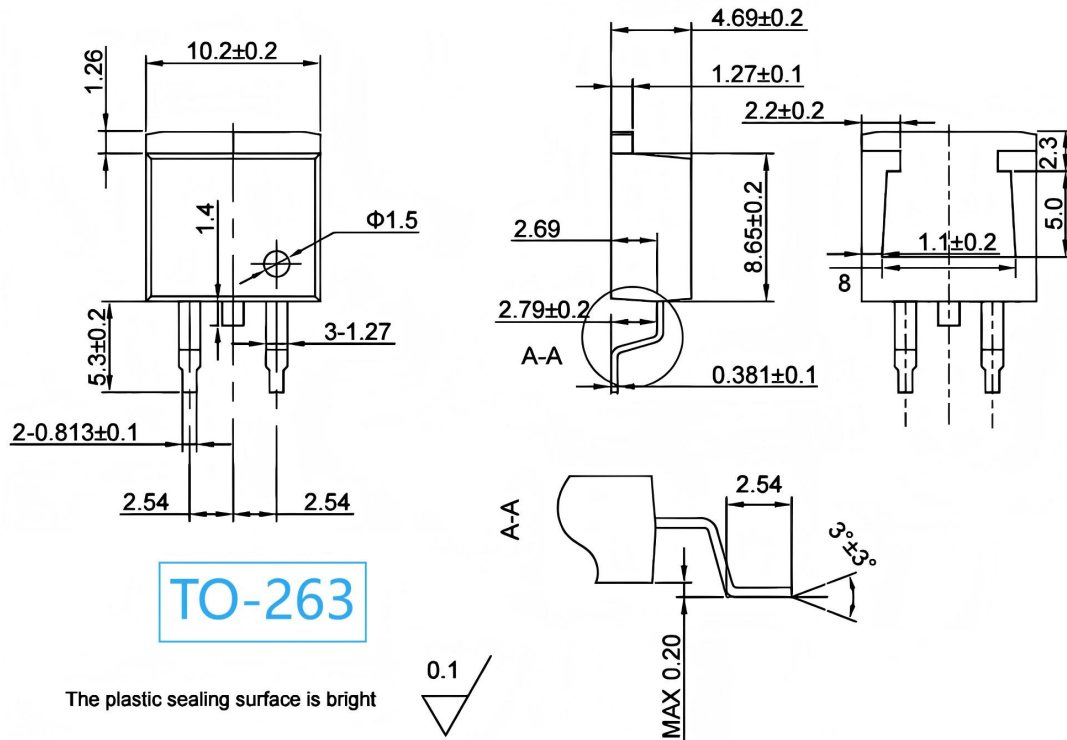
Marking	Package
MS30N90ICE0	TO-263
MS30N90ICC0	TO-247

Typical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)





Package Mechanical DATA



Notes:

1. Unmarked tolerance ± 0.15 mm; unmarked $R < 0.15$ mm
2. The resin body is not allowed to have defects, shrinkage holes, cracks, bubbles and other harmful defects
3. The drawing indicates that the leg has reinforcement
4. Unit : mm

